

forming source and drain regions connected to the channel region in a semiconductor film that is formed on a surface of an insulating substrate; and forming a recombination center that captures carriers in the channel region by introducing an impurity into said channel region.

2. (Amended) The method of manufacturing a thin-film transistor according to Claim 1, said impurity being at least one kind selected from the group including inert gases, metals, Group III elements, Group IV elements and Group V elements.

3. (Twice Amended) The method of manufacturing a thin-film transistor according to Claim 1, wherein a process of introducing said impurity into said channel region is carried out by injecting the impurity from a surface side of said channel region.

4. (Amended) The method of manufacturing a thin-film transistor according to Claim 3, wherein a process of introducing said impurity into said channel region is carried out, after a crystallization process on a semiconductor film so as to form said channel region, by injecting the impurity from a surface side of said channel region.

5. (Amended) The method of manufacturing a thin-film transistor according to Claim 3, wherein a process of introducing said impurity into said channel region is carried out, after a crystallization process on a semiconductor film so as to form said channel region, by injecting the impurity from a surface side of said channel region before a process of forming said gate electrode on a surface side of the channel region.

6. (Amended) The method of manufacturing a thin-film transistor according to Claim 3, wherein a process of introducing said impurity into said channel region is carried out, after said gate insulating film and said gate electrode are sequentially formed on a

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surface side of said channel region, by injecting the impurity from a surface side of said gate electrode before an interlayer insulating film is formed on a surface side of the gate electrode.

7. (Twice Amended) The method of manufacturing a thin-film transistor according to Claim 3, an average projected range of the impurity in said process of introducing an impurity being from a center in a direction of thickness of said channel region to an interface between the channel region and the gate insulating film.

8. (Twice Amended) The method of manufacturing a thin-film transistor according to Claim 3, an average projected range of the impurity in said process of introducing an impurity being from a center in a direction of thickness of said channel region to an interface between the channel region and a layer located on said substrate side.

9. (Amended) The method of manufacturing a thin-film transistor according to Claim 1, a process of introducing said impurity to said channel region being carried out by impurity diffusion from an impurity diffusion source arranged at a lower layer side of said channel region.

10. (Amended) The method of manufacturing a thin-film transistor according to Claim 9, said impurity diffusion being carried out in a crystallization process on a semiconductor film so as to form said channel region.

11. (Twice Amended) The method of manufacturing a thin-film transistor according to Claim 4, said crystallization process being laser annealing on a semiconductor film so as to form said channel region.

12. (Twice Amended) The method of manufacturing a thin-film transistor according to Claim 1, each process carried out after introducing said impurities to said channel region being carried out at a temperature below 400°C.